Ordering number : ENA1123

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

EFC4618R-P — General-Purpose Switching Device Applications

Features

- 2.5V drive
- Best suited for LiB charging and discharging switch
- Common-drain type

Specifications

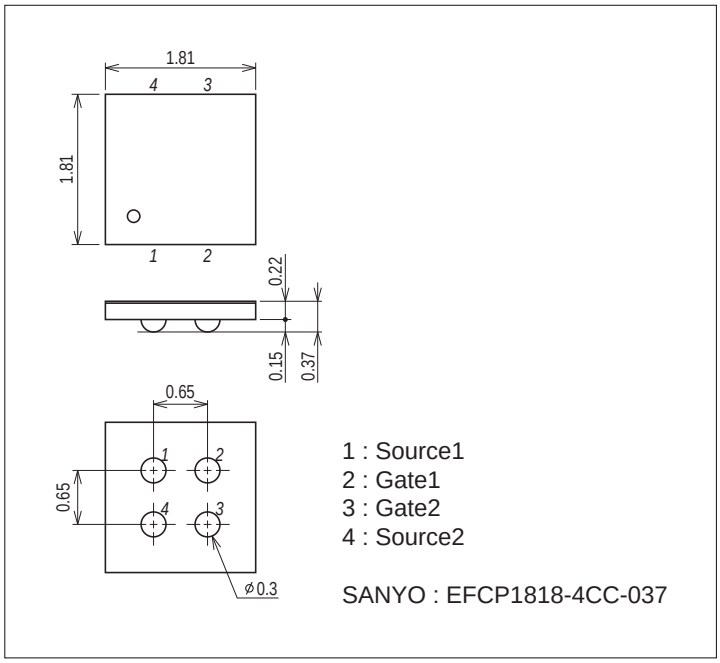
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Source-to-Source Voltage	V_{SSS}		24	V
Gate-to-Source Voltage	V_{GSS}		±12	V
Source Current (DC)	I_S		6	A
Source Current (Pulse)	I_{SP}	PW≤10μs, duty cycle≤1%	60	A
Total Dissipation	P_T	When mounted on ceramic substrate (5000mm²×0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Package Dimensions

unit : mm (typ)

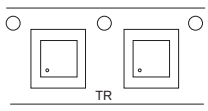
7069-001



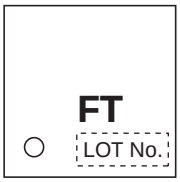
Product & Package Information

- Package : EFCP
- JEITA, JEDEC : -
- Minimum Packing Quantity : 5,000 pcs./reel

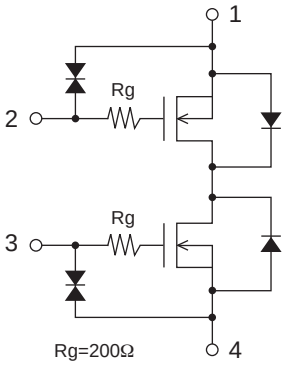
Packing Type : TR



Marking



Electrical Connection

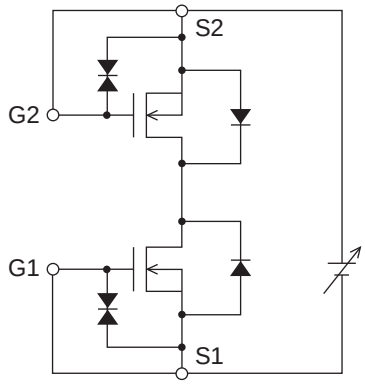


Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions		Ratings min	Ratings typ	Ratings max	Unit
Source-to-Source Breakdown Voltage	$V_{(BR)SSS}$	I_S=1mA, V_{GS}=0V	Test Circuit 1	24			V
Zero-Gate Voltage Source Current	I_{SSS}	V_{SS}=20V, V_{GS}=0V	Test Circuit 1			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{SS}=0V	Test Circuit 2			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{SS}=10V, I_S=1mA	Test Circuit 3	0.5		1.3	V
Forward Transfer Admittance	| yfs |	V_{SS}=10V, I_S=3A	Test Circuit 4		6.5		S
Static Source-to-Source On-State Resistance	R_{SS}(on)1	I_S=3A, V_{GS}=4.5V	Test Circuit 5	13.5	19.8	23	mΩ
	R_{SS}(on)2	I_S=3A, V_{GS}=4.0V	Test Circuit 5	14	20.5	24	mΩ
	R_{SS}(on)3	I_S=3A, V_{GS}=3.7V	Test Circuit 5	14.5	21	25.5	mΩ
	R_{SS}(on)4	I_S=3A, V_{GS}=3.1V	Test Circuit 5	14.9	23	30	mΩ
	R_{SS}(on)5	I_S=3A, V_{GS}=2.5V	Test Circuit 5	18.5	27	35	mΩ
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.	Test Circuit 7		200		ns
Rise Time	t_r	See specified Test Circuit.	Test Circuit 7		815		ns
Turn-OFF Delay Time	t_d(off)	See specified Test Circuit.	Test Circuit 7		1840		ns
Fall Time	t_f	See specified Test Circuit.	Test Circuit 7		1770		ns
Total Gate Charge	Qg	V_{SS}=10V, V_{GS}=4.5V, I_S=6A			25.4		nC
Forward Source-to-Source Voltage	$V_{F(S-S)}$	I_S=3A, V_{GS}=0V	Test Circuit 6		0.76	1.2	V

Test circuits are example of measuring FET1 side

Test Circuit 1
V_{SSS} / I_{SSS}



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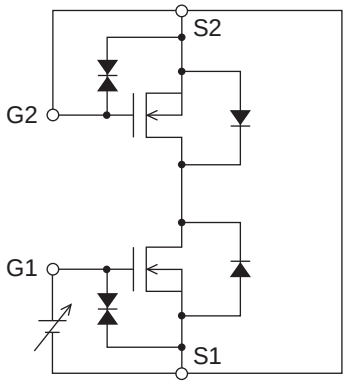
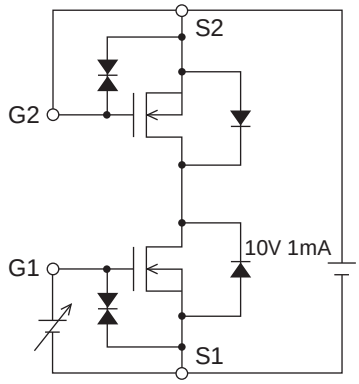
Test Circuit 2
I_{GSS}(+) / (−)



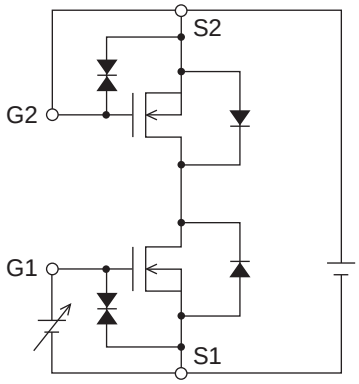
IT11566

Test Circuit 3
V_{GS}(off)



IT11567

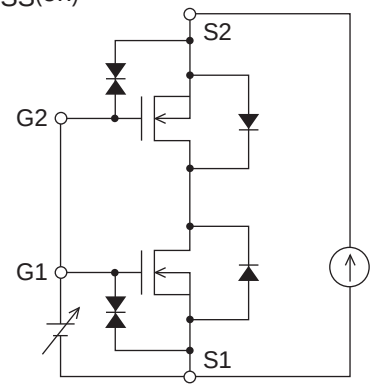
Test Circuit 4
| yfs |



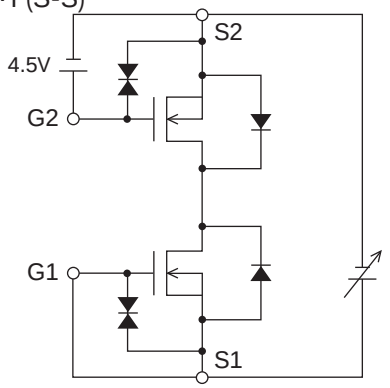
IT11568

* Note: Connect the mesurement terminal reversely if you want to measure the FET2 side.

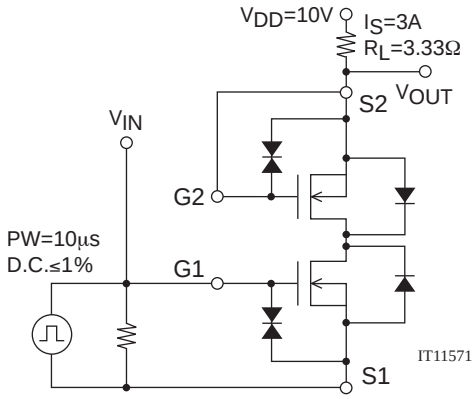
Test Circuit 5
$R_{SS(on)}$



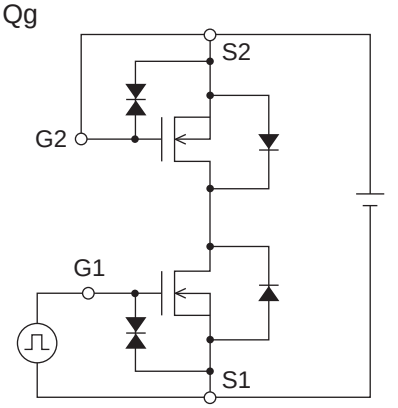
Test Circuit 6
$V_{F(S-S)}$



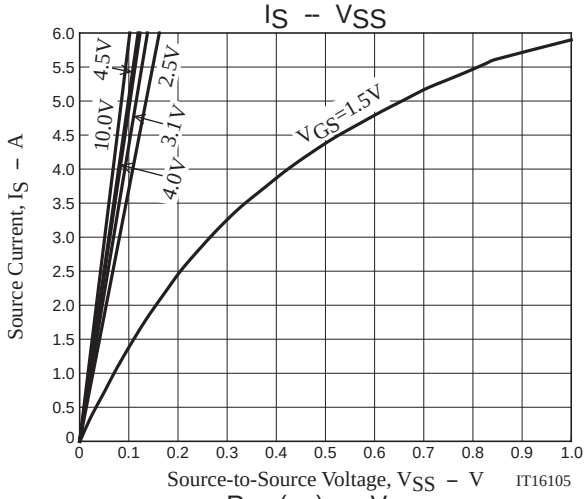
Test Circuit 7
$t_{d(on)}$, t_r, $t_{d(off)}$, t_f

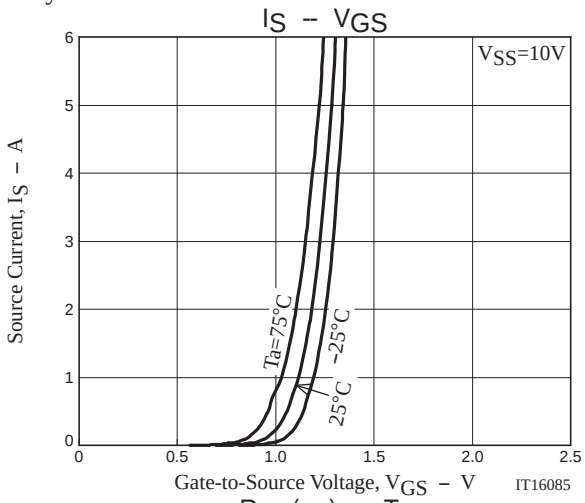


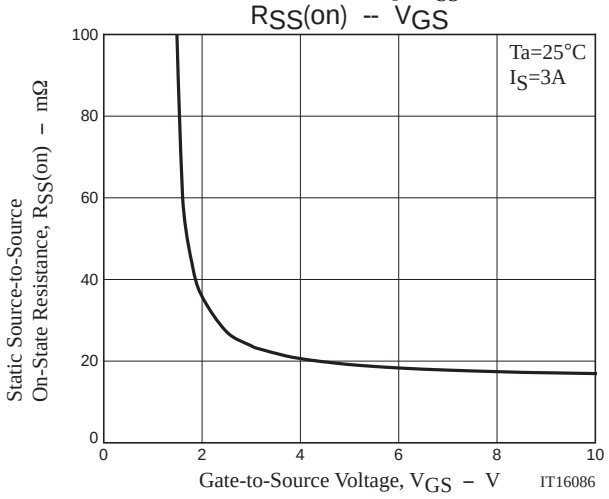
Test Circuit 8
Qg

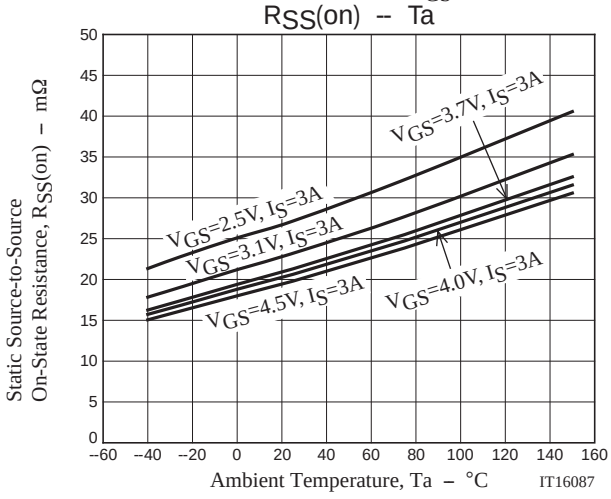


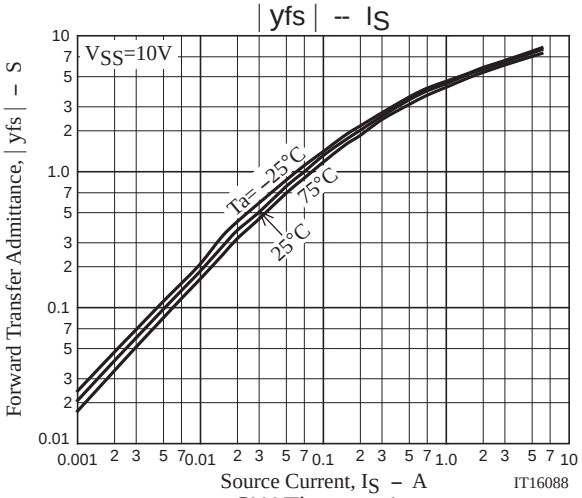
* Note: Connect the mesurement terminal reversely if you want to measure the FET2 side.

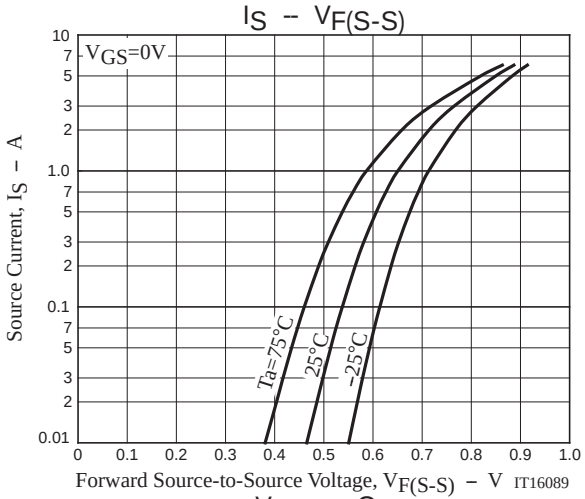


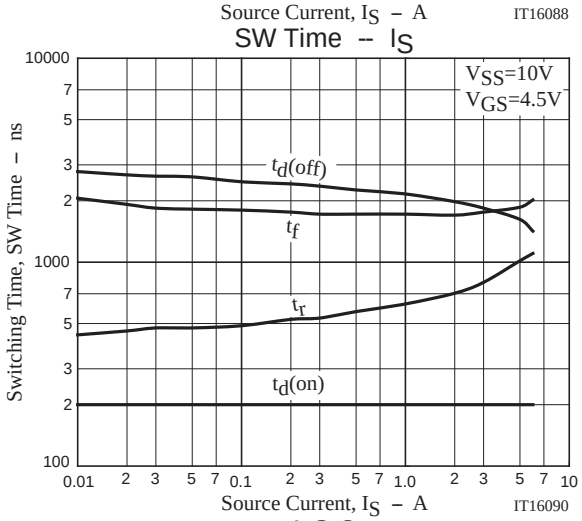


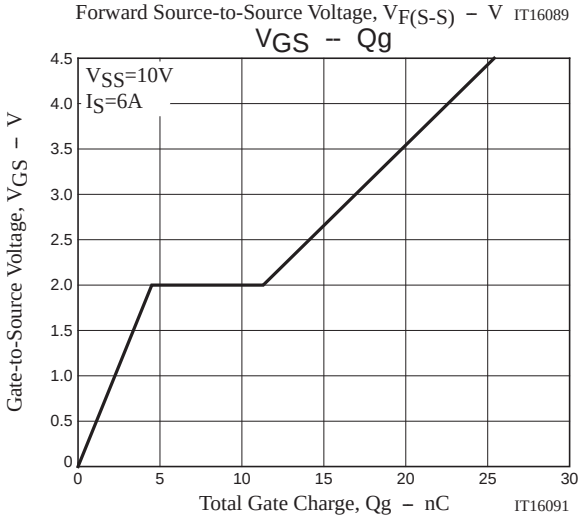


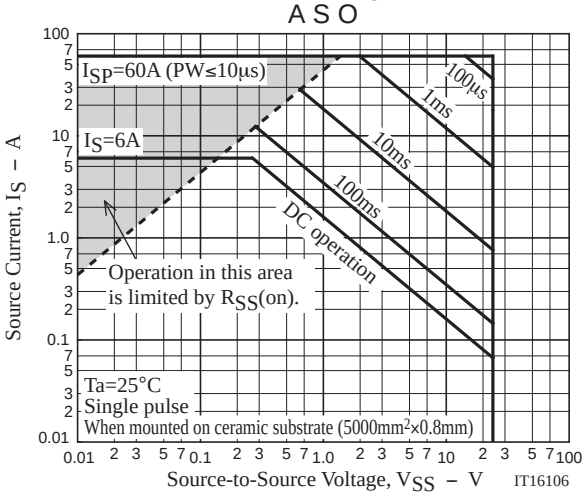


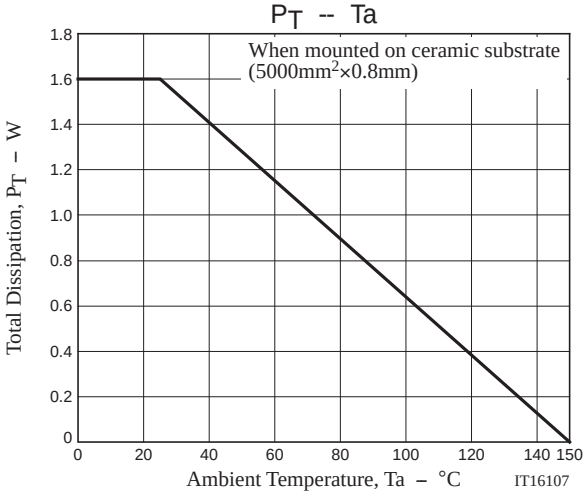

| yfs | -- IS
VSS=10V
Ta= –25°C
75°C
25°C
Forward Transfer Admittance, | yfs | – S
Source Current, IS – A
IT16088


IS -- VF(S-S)
VGS=0V
Ta=75°C
25°C
–25°C
Source Current, IS – A
Forward Source-to-Source Voltage, VF(S-S) – V
IT16089


SW Time -- IS
VSS=10V
VGS=4.5V
td(off)
tf
tr
td(on)
Switching Time, SW Time – ns
Source Current, IS – A
IT16090


VGS -- Qg
VSS=10V
IS=6A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT16091


A S O
ISP=60A (PW≤10μs)
IS=6A
100μs
1ms
10ms
100ms
DC operation
Operation in this area
is limited by RSS(on).
Ta=25°C
Single pulse
When mounted on ceramic substrate (5000mm2×0.8mm)
Source Current, IS – A
Source-to-Source Voltage, VSS – V
IT16106


PT -- Ta
When mounted on ceramic substrate
(5000mm2×0.8mm)
Total Dissipation, PT – W
Ambient Temperature, Ta – °C
IT16107

Note on usage : Since the EFC4618R-P is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

This catalog provides information as of November, 2011. Specifications and information herein are subject to change without notice.